PNP Transistor Bare Die, 2N2906A

Rev 1.0
02/09/17

General purpose medium power amplifier or switch in bare die form
Complement to NPN 2N2222A

Features:

- Minimum gain of 40 across current range
- Low Collector-Emitter Saturation Voltage
- Characterized at temperature extremes
- High Reliability Gold Back Metal
- High Reliability tested grades for Military + Space

Ordering Information:

The following part suffixes apply:

- No suffix - MIL-STD-750 /2072 Visual Inspection
- "**H**" - MIL-STD-750 /2072 Visual Inspection
  + MIL-PRF-38534 Class H LAT
- "**K**" - MIL-STD-750 /2072 Visual Inspection
  + MIL-PRF-38534 Class K LAT

LAT = Lot Acceptance Test.

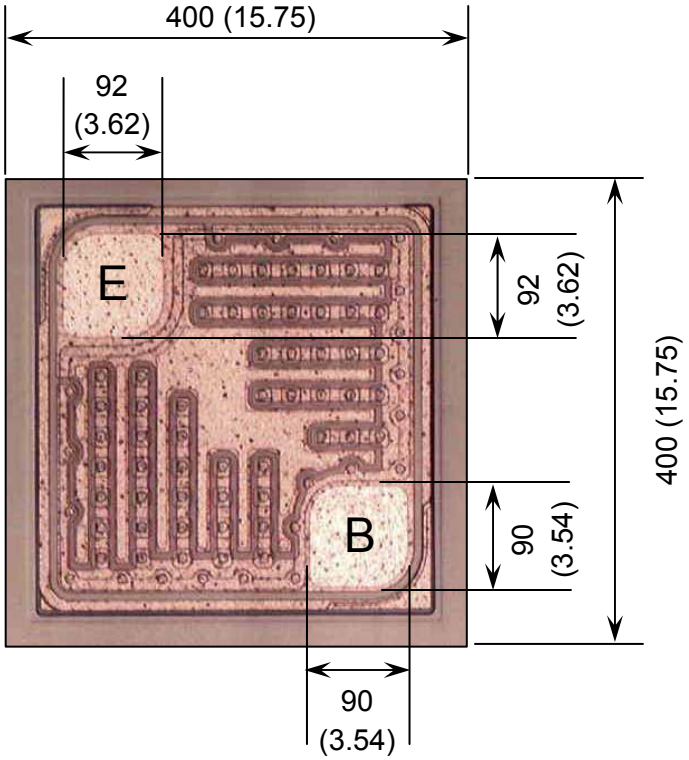
For further information on LAT process flows see below.

www.siliconsupplies.com\quality\bare-die-lot-qualification

Supply Formats:

- Default – Die in Waffle Pack (400 per tray capacity)
- Sawn Wafer on Tape – Specific request
- Unsawn Wafer – Specific request
- With additional electrical selection – Specific request
- Sawn as pairs or adjacent pair pick – Specific request

Die Dimensions in µm (mils)



E = EMITTER **B** = BASE

DIE BACK = COLLECTOR

Mechanical Specification

Die Size (Excluding Saw Street)	400 x 400 9.84 x 10.63	µm mils
Base Pad Size	90 x 90 3.54 x 3.54	µm mils
Emitter Pad Size	92 x 92 3.62 x 3.62	µm mils
Die Thickness	180 (±20) 7.09 (±0.79)	µm mils
Top Metal Composition	Al - 1.3µm	
Back Metal Composition	AuAs - 0.9µm	

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Absolute Maximum Ratings T_A = 25°C unless otherwise stated

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-60	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-600	mA
Junction Temperature	T_J	150	°C
Storage Temperature	T_{stg}	-55 to 150	°C

Electrical Characteristics T_A = 25°C unless otherwise stated

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	I_C = -10µA	-60	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = -10mA	-60	-	-	V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	I_E = -10µA	-5	-	-	V
Collector Cut-off Current	I_{CEX}	V_{CE} = -30V, V_{EB} = -0.5V	-	-	-50	nA
	I_{CBO}	V_{CB} = -50V	-	-	-20	nA
Emitter Cut-off Current	I_{EBO}	V_{EB} = -4V	-	-	-50	nA
ON CHARACTERISTICS						
Forward-Current Transfer Ratio	h_{FE}	V_{CE} = -10V, I_C = -0.1mA	40	-	-	-
		V_{CE} = -10V, I_C = -1mA	40	-	-	-
		V_{CE} = -10V, I_C = -10mA	40	-	-	-
		V_{CE} = -10V, I_C = -150mA	40	-	120	-
		V_{CE} = -10V, I_C = -500mA	40	-	-	-
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = -150mA, I_B = -15mA	-	-	-0.4	V
		I_C = -500mA, I_B = -50mA	-	-	-1.6	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C = -150mA, I_B = -15mA	-	-	-1.3	V
		I_C = -500mA, I_B = -50mA	-	-	-2.6	V
SMALL SIGNAL CHARACTERISTICS[1]						
Transition Frequency	f_T	V_{CE} = -20V, I_E = 50mA	200	-	-	MHz
Output Capacitance	C_{obo}	V_{CB} = -10V, I_E = 0, f = 1MHz	-	-	8	pF
Input Capacitance	C_{ibo}	V_{EB} = -2V, I_C = 0, f = 1MHz	-	-	30	
SWITCHING CHARACTERISTICS[1]						
Delay Time	t_d	V_{CC} = -30V, I_C= -150mA, I_{B1}= -15mA	-	-	10	ns
Rise Time	t_r		-	-	40	
Storage Time	t_s	V_{CC} = -6V, I_C = -150mA I_{B1} = I_{B2} = -15mA	-	-	80	
Fall Time	t_f		-	-	30	

Note 1: Not production testing in die form, characterized by chip design and tested in package LAT.

Typical Electrical Characteristics

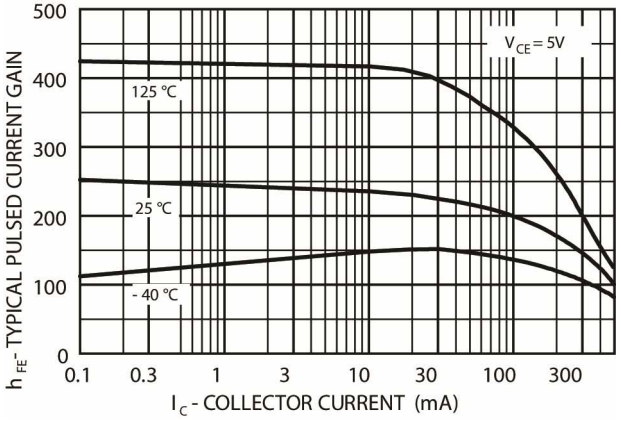

Fig 1 - Typical Pulsed Current Gain versus Collector Current

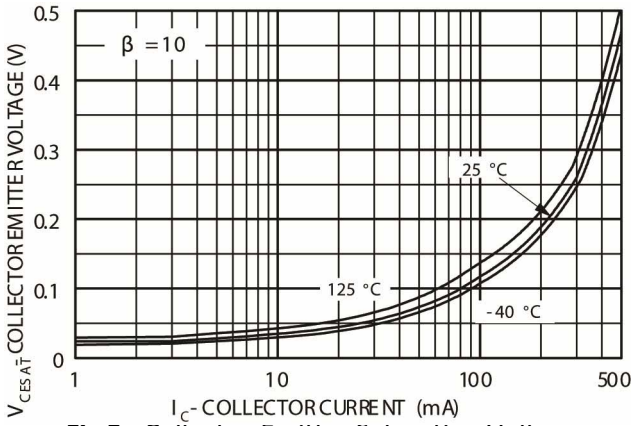

Fig 2 - Collector-Emitter Saturation Voltage versus Collector Current

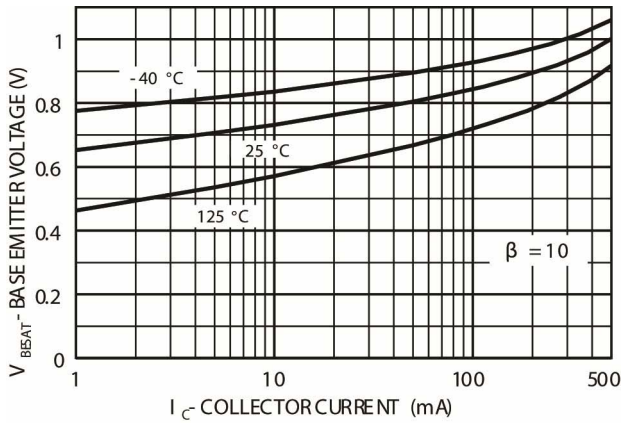

Fig 3 - Base-Emitter Saturation Voltage versus Collector Current

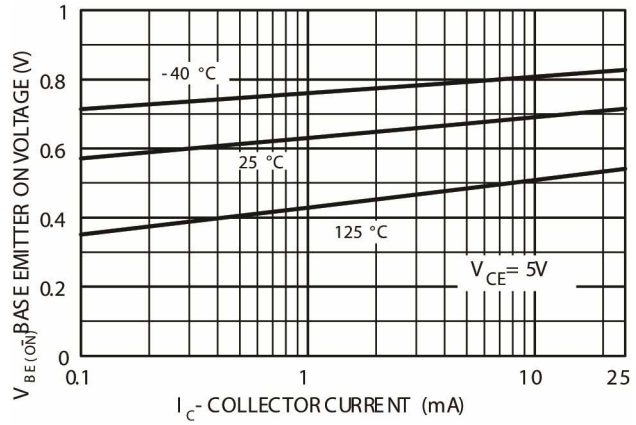

Fig 4 - Base-Emitter ON Voltage versus Collector Current

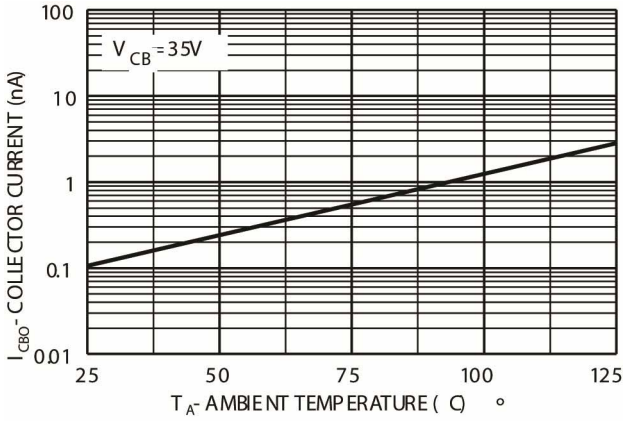

Fig 5 - Collector-Cut-off Current versus Ambient Temperature

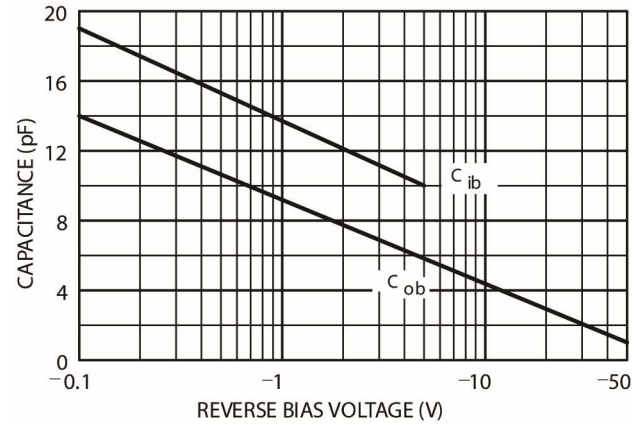

Fig 6 - Capacitance versus Reverse Bias Voltage

Typical Electrical Characteristics (Continued)

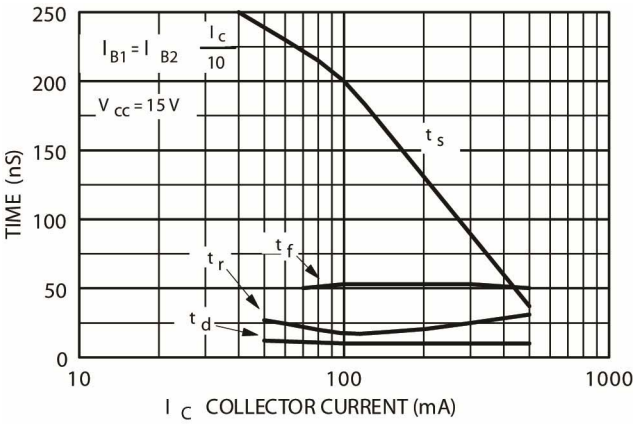

Fig 7 – Switching Times versus Collector Current

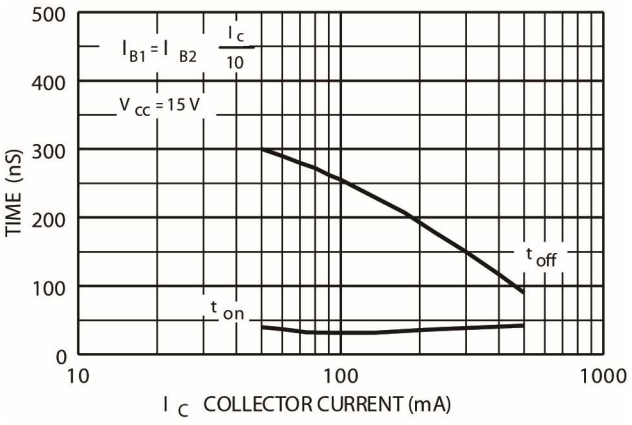

Fig 8 - Turn On and Turn Off Times versus Collector Current

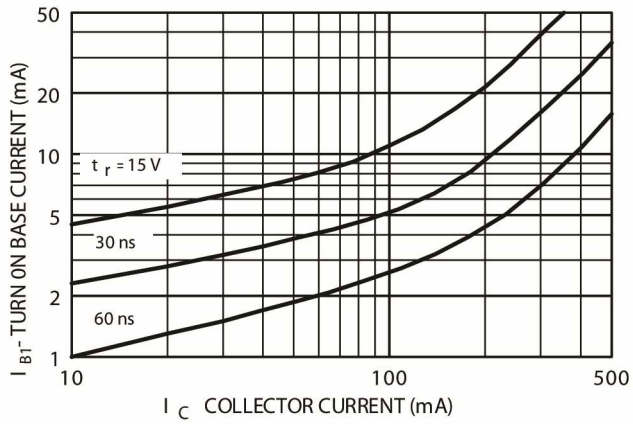

Fig 9 – Rise Time versus Collector and Turn On Base Currents

Typical Electrical Characteristics (Continued)

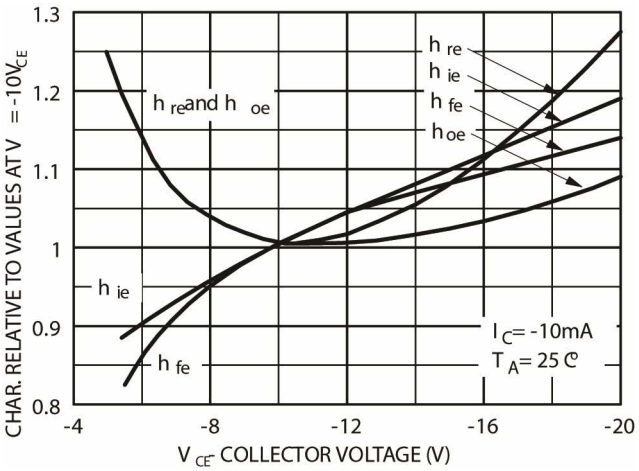

Fig 10 – Common Emitter Characteristics

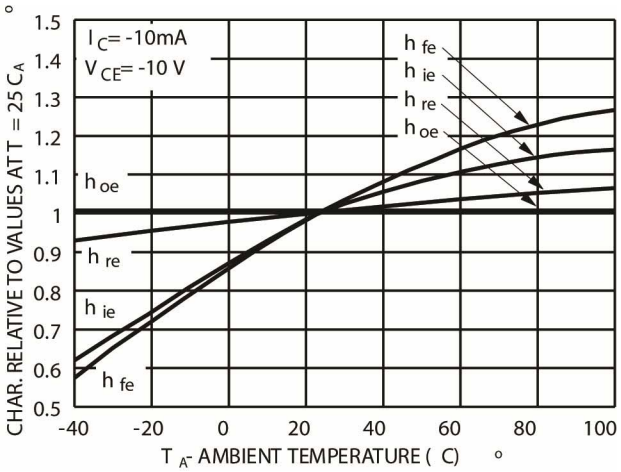

Fig 11 – Common Emitter Characteristics

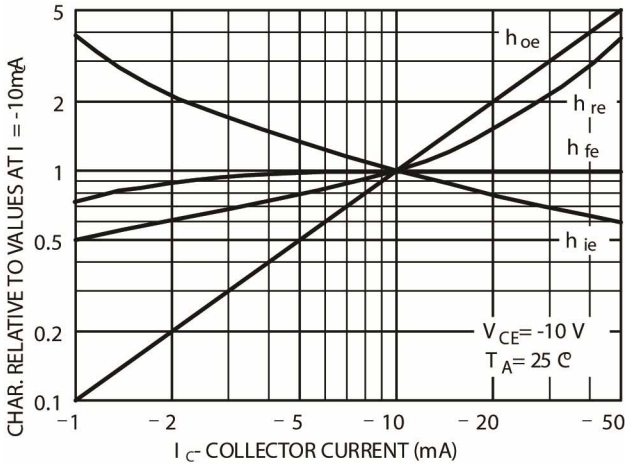

Fig 12 – Common Emitter Characteristics